Raymond T Tung

List of Publications by Citations

19 papers	2,346 citations	10 h-index	20 g-index
20 ext. papers	2,587 ext. citations	6.6 avg, IF	6.03 L-index

#	Paper	IF	Citations
19	Recent advances in Schottky barrier concepts. *Materials Science and Engineering Reports*, **2001**, 35, 1-138	30.9	915
18	The physics and chemistry of the Schottky barrier height. *Applied Physics Reviews*, **2014**, 1, 011304	17.3	595
17	Chemical bonding and fermi level pinning at metal-semiconductor interfaces. *Physical Review Letters*, **2000**, 84, 6078-81	7.4	301
16	Formation of an electric dipole at metal-semiconductor interfaces. *Physical Review B*, **2001**, 64,	3.3	253
15	Controlling semiconductor/metal junction barriers by incomplete, nonideal molecular monolayers. *Journal of the American Chemical Society*, **2006**, 128, 6854-69	16.4	95
14	Tuning the electrical properties of Si nanowire field-effect transistors by molecular engineering. *Small*, **2009**, 5, 2761-9	11	72
13	Controlling Au/n-GaAs junctions by partial molecular monolayers. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 3438-3451	1.6	25
12	Band offset formation at semiconductor heterojunctions through density-based minimization of interface energy. *Physical Review B*, **2016**, 94,	3.3	13
11	Charge Density and Band Offsets at Heterovalent Semiconductor Interfaces. *Advanced Theory and Simulations*, **2018**, 1, 1700001	3.5	12
10	Controlled modification of Schottky barrier height by partisan interlayer. *Solid State Communications*, **2011**, 151, 1641-1644	1.6	11
9	Bidirectional Control of Silicon Surface Potential by Means of Molecular Coverage. *Journal of Physical Chemistry C*, **2010**, 114, 18674-18678	3.8	9
8	Inhomogeneous ohmic contacts: Barrier height and contact area determination. *Applied Physics Letters*, **2012**, 101, 051604	3.4	9
7	Schottky barrier height systematics studied by partisan interlayer. *Thin Solid Films*, **2014**, 557, 254-257	2.2	8
6	Effect of metal interaction on the Schottky barrier height on adsorbate-terminated silicon surfaces. *Applied Surface Science*, **2013**, 284, 720-725	6.7	7
5	Modification of Schottky barrier height on Si (111) by Ga-termination. *Surface Science*, **2013**, 610, 48-52	1.8	6
4	Quantitative explanation of the Schottky barrier height. *Physical Review B*, **2021**, 103,	3.3	6
3	Bulklike band-offset mystery solved through energy minimization: Lessons from perovskite oxide heterojunctions. *Physical Review B*, **2019**, 99,	3.3	5

2	From NiSi2 experiments to density functional theory calculations: How the Schottky barrier mystery was solved. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 020803	2.9	1
1	Combined UHV and Liquid Phase (CULP) Processing of Self-assembled Nanostructures. *Materials Research Society Symposia Proceedings*, **2005**, 879, 1		